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Medium energy ion scattering of Gr on SiC(0001) and Si(100)

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Depth profiling of graphene with high-resolution ion beam analysis is a practical method for analysis of monolayer thicknesses of graphene. Not only is the energy resolution sufficient to resolve graphene from underlying SiC but by use of isotope labeling it is possible to tag graphene generated from reacted ethylene. Furthermore, we are able to analyze graphene supported by oxidized Si(100) substrates, allowing the study of graphene films grown by chemical vapor deposition on metal and transferred to silicon. This introduces a powerful method to explore the fundamentals of graphene formation. © 2011 American Institute of Physics. [doi:10.1063/1.3565968]

Characterization of graphene formation on surfaces is an experimental challenge that is pivotal to developing carbon-based electronic devices. Due to the extreme thinness of two-dimensional carbon layers, conventional tools of solid-state physics are hard pressed to address structural issues that are presented. Lateral coherence can be studied with probes such as transmission electron microscopy,1 scanning tunneling microscopy,2 or low energy electron microscopy,3 and structural information can also be garnered with Raman scattering.4 However, these techniques are not generally used to learn about buried interfaces. Medium energy ion scattering (MEIS) offers a unique capability of depth profiling with isotopic specificity that can be used to study growth modes in a quantitative manner. In this letter, we will demonstrate that MEIS can be applied to graphene, opening up an avenue for research into challenging questions concerning this electronic material. Already, MEIS has been used to study SiC oxidation by diffusion of oxygen through graphene.5

MEIS has been widely applied as a probe of thin films and surfaces, offering quantitative analysis based on well understood Rutherford scattering.67 Results can be accurately modeled with simulations based on independently determined parameters, such as scattering cross section and rate of energy loss in a host material.8 However, to apply an ion beam probe to a graphene layer, several requirements must be met. First, the sample must be macroscopic, since the probe samples an area of several square millimeters. Second, the background from the substrate must be suppressed enough for the carbon signal to be detected. Both of these requirements can be met when the sample is Gr/SiC; large area samples have been demonstrated on SiC substrates, and the use of a channeling geometry reduces the substrate signal by two orders of magnitude. This means that ion beam analysis can at least be attempted for Gr/SiC. Finally, we must consider whether there is sufficient resolution to discriminate between surface Gr and the carbon in the SiC. The energy loss of a 100 keV proton traveling through carbon is 13 eV/1015 atoms/cm2. The areal density of a monolayer (ML) of Gr is 3.9×1015/cm2. Including a geometric factor of 3.9 based on the angle of incidence (0°) and exit angle (20°), the energy loss for each layer of graphene is 200 eV. Since MEIS has been demonstrated with an energy resolution of better than 150 eV for 100 keV protons, it is certainly feasible to separate the backscatter peak of a multilayer graphene film from a SiC substrate.

As a test of applicability of MEIS to Gr/SiC, we examined two films with differing thicknesses of graphene, both grown by sublimation of Si from Si-face SiC(0001) at high temperatures9 in accordance with established techniques for generating smooth layers.3 One sample was grown for 10 min at 1180°C, and a second sample was grown at about 20 °C higher temperature to generate a thicker Gr layer. After processing, the samples were transferred through air to the MEIS system. Figure 1 shows the carbon and silicon backscatter peaks from the two samples. The film grown at higher temperature has a broader carbon peak with slightly higher intensity compared to the low temperature film. The increased width of the peak is due to greater energy losses.

FIG. 1. (Color online) Backscattering spectra for two different thicknesses of Gr/SiC(0001). The carbon peak shows increased width for the thicker film, demonstrating that the energy resolution is adequate to yield depth information. The silicon peak is displaced toward lower energy for the thicker film, due to the stopping power of the graphene.
experienced by protons as they traverse the graphene, indicating a thicker film. An additional distinction can be seen in the position of the leading edge of the Si backscatter peak, which occurs at lower energy for the thicker film. This is also an indication of a thicker graphene layer, since the protons lose more energy going through the graphene to reach the underlying SiC, as well as reemerging to the vacuum. Note that the top layers of the SiC are visible to the ion beam, since the graphene does not shadow the underlying SiC. However, below the SiC surface peak the ions channel in crystalline SiC, reducing the yield to small background intensity. The Si peak is entirely due to the SiC, while the carbon peak contains contributions from both Gr and SiC.

Quantitative models of the spectra, drawn as smooth curves in Fig. 1, show that the samples consist of 1.9 and 2.7 ML of graphene. In our models, the SiC contributes equal amounts to the Si and carbon peaks after normalizing to the Rutherford cross section. This result demonstrates that MEIS cannot just discriminate between graphene layers of different thicknesses, but has the capability of depth profiling, since the stopping power of an added layer of graphene results in measurable shifts in spectral features.

Simulations of MEIS results support the assertion that we can determine graphene thickness with submonolayer sensitivity. To illustrate this, we have plotted a spectrum with 1.9 ML of graphene along with simulated results with coverages varying by 0.5 ML (Fig. 2). When the graphene thickness is altered from the optimum fit, large discrepancies occur for both the carbon peak width and the location of the Si peak. The inset for Fig. 2 shows the goodness of fit based on an r-factor as a function of graphene thickness. A sharp minimum can be found near 1.9 ML, indicating that deviations between experiment and simulation can be quantitatively assessed and used to guide evaluation of data.

Additional information about graphene layers can be gathered by using $^{13}$C$_2$H$_4$ as a gas source. Since scattering kinematics are dependent on target mass, protons backscattered from $^{13}$C have a greater kinetic energy than protons scattered from $^{12}$C. This gives the capability of separating a graphene layer generated by decomposition of $^{13}$C$_2$H$_4$ from the substrate signal, which should be predominantly $^{12}$C. In Fig. 3, we show a spectrum from a SiC sample that was cleaned by heating to 850 °C in $1 \times 10^{-6}$ Torr disilane, followed by exposure to $2 \times 10^{-5}$ Torr of $^{13}$C$_2$H$_4$ at 1140 °C. After transfer through air, the sample was degassed for 1 min at 750 °C to remove contaminants. Two carbon peaks are visible in the spectra. A sharp peak at 81.1 keV due to backscattering from surface $^{13}$C and a broad peak centered at 79.5 keV due to $^{12}$C in the top layers of the SiC. We have plotted both carbon peaks on the same depth scale in Fig. 3(b). The $^{12}$C intensity peaks below the surface of the sample, since the SiC is mostly covered by graphene. The smooth curves plotted on the data were generated from a model with 1.5 ML of graphene consisting of 88% $^{13}$C, covering 95% of the surface. The model includes 32% $^{13}$C (relative to total C) in the top layers of the SiC. We have succeeded in growing a graphene layer composed almost entirely of $^{13}$C covering nearly the entire sample. It is not clear whether there is some small intermixing of $^{13}$C with the underlying SiC, or whether our model underestimates the tail of the $^{13}$C signal. Nonetheless, the results establish that the use of carbon isotopes combined with MEIS is a potential means for tracking the dynamics of graphene growth on SiC substrates.

Although this letter is mostly concerned with Gr/SiC, MEIS analysis is not limited to SiC. In fact, all that is required is a large area graphene film supported by a single crystal substrate. To illustrate this point, we turn to graphene films created by chemical vapor deposition (CVD) on metal, followed by transfer to oxidized Si substrates. Following procedures similar to Ref. 11, a polycrystalline Cu foil was exposed to an ambient of 0.5 Torr of ethylene for 10 min at 975 °C. Deposition was preceded by an $in situ$ 10 min forming gas anneal at the growth temperature. Afterwards, the sample was bonded to poly(methyl methacrylate) (PMMA) and the Cu was dissolved in FeCl$_3$. The PMMA was removed after bonding to a Si sample with a native oxide present. A proton beam is able to penetrate through the native oxide
layer to channel in the crystalline Si, reducing the background to the levels needed for carbon analysis by MEIS. Consequently, we are able to gather data on Gr coverage as ground to the levels needed for carbon analysis by MEIS. Annealing not only improves the shape of t...